

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

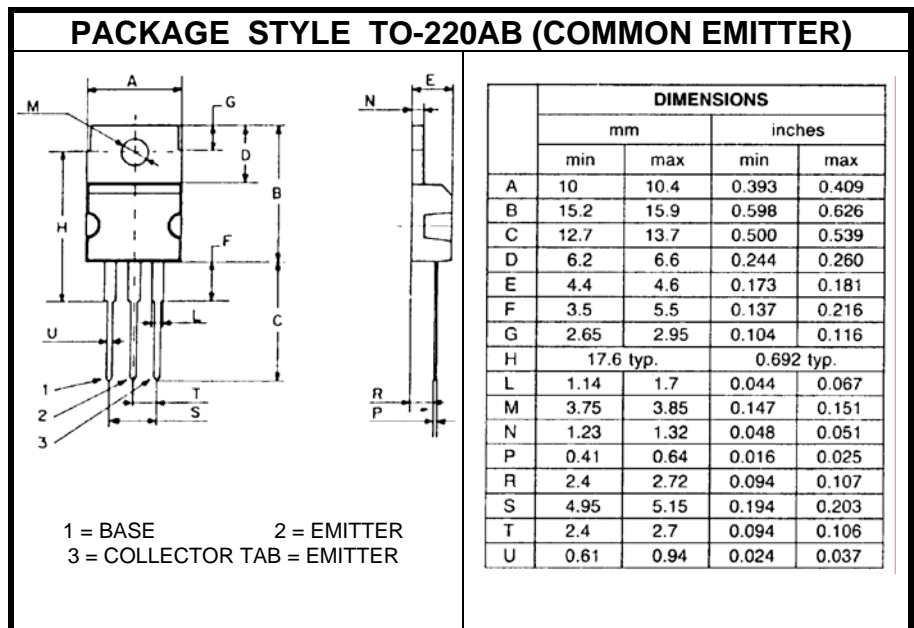
The **ASI 2SC1971** is Designed for RF power amplifiers on VHF band mobile radio applications.

**FEATURES INCLUDE:**

- Replaces Original **2SC1971** in Most Applications
- High Gain Reduces Drive Requirements
- Economical **TO-220CE** Package

**MAXIMUM RATINGS**

$I_C$	2.0 A
$V_{CBO}$	35 V
$P_{DISS}$	12.5 W @ $T_C = 25\text{ }^\circ\text{C}$
$T_{STG}$	-55 $^\circ\text{C}$ to +150 $^\circ\text{C}$
$\theta_{JC}$	10 $^\circ\text{C/W}$


**CHARACTERISTICS**  $T_C = 25\text{ }^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 50\text{ mA}$	17			V
$BV_{CBO}$	$I_C = 10\text{ mA}$	35			V
$BV_{EBO}$	$I_E = 5.0\text{ mA}$	4.0			V
$I_{CBO}$	$V_{CES} = 25\text{ V}$			500	$\mu\text{A}$
$I_{EBO}$	$V_{EB} = 3.0\text{ V}$			500	$\mu\text{A}$
$h_{FE}$	$V_{CE} = 10\text{ V}$ $I_C = 100\text{ mA}$	10	50	180	---
$C_{OB}$	$V_{CB} = 30\text{ V}$ $f = 1.0\text{ MHz}$		15		pF
$G_{PE}$	$V_{CC} = 13.5\text{ V}$ $P_{IN} = 0.6\text{ W}$ $f = 175\text{ MHz}$	10			dB
$\eta$		60	70		%
$P_{OUT}$		6.0	7.0		W